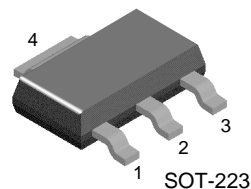


## BSP52

### NPN Darlington Transistor

- This device is designed for applications requiring extremely high current gain at collector currents to 500mA.
- Sourced from process 03.



1. Base 2. Collector 3. Emitter

### Absolute Maximum Ratings\* $T_A=25^\circ\text{C}$ unless otherwise noted

| Symbol         | Parameter  | Value       | Units            |
|----------------|--|-------------|------------------|
| $V_{CES}$      | Collector-Emitter Voltage                        | 80          | V                |
| $V_{CBO}$      | Collector-Base Voltage                           | 90          | V                |
| $V_{EBO}$      | Emitter-Base Voltage                             | 5           | V                |
| $I_C$          | Collector Current - Continuous                   | 800         | mA               |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range | - 55 ~ +150 | $^\circ\text{C}$ |

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of  $150^\circ\text{C}$ .
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Electrical Characteristics $T_A=25^\circ\text{C}$ unless otherwise noted

| Symbol                     | Parameter                            | Test Conditions  | Min.         | Typ. | Max. | Units         |
|----------------------------|--------------------------------------|--|--------------|------|------|---------------|
| <b>Off Characteristics</b> |                                      |  |              |      |      |               |
| $V_{(BR)CBO}$              | Collector-Base Breakdown Voltage     | $I_C = 100\mu\text{A}, I_E = 0$  | 90           |      |      | V             |
| $V_{(BR)EBO}$              | Emitter-Base Breakdown Voltage       | $I_E = 10\mu\text{A}, I_C = 0$   | 5            |      |      | V             |
| $I_{CES}$                  | Collector Cutoff Current             | $V_{CE} = 80\text{V}, V_{BE} = 0$  |              |      | 10   | $\mu\text{A}$ |
| $I_{EBO}$                  | Emitter Cutoff Current               | $V_{EB} = 4.0\text{V}, I_C = 0$  |              |      | 10   | $\mu\text{A}$ |
| <b>On Characteristics</b>  |                                      |  |              |      |      |               |
| $h_{FE}$                   | DC Current Gain                      | $I_C = 150\text{mA}, V_{CE} = 10\text{V}$<br>$I_C = 500\text{mA}, V_{CE} = 10\text{V}$ | 1000<br>2000 |      |      |               |
| $V_{CE(sat)}$              | Collector-Emitter Saturation Voltage | $I_C = 500\text{mA}, I_B = 0.5\text{mA}$   |              |      | 1.3  | V             |
| $V_{BE(sat)}$              | Base-Emitter Saturation Voltage      | $I_C = 500\text{mA}, I_B = 0.5\text{mA}$   |              |      | 1.9  | V             |

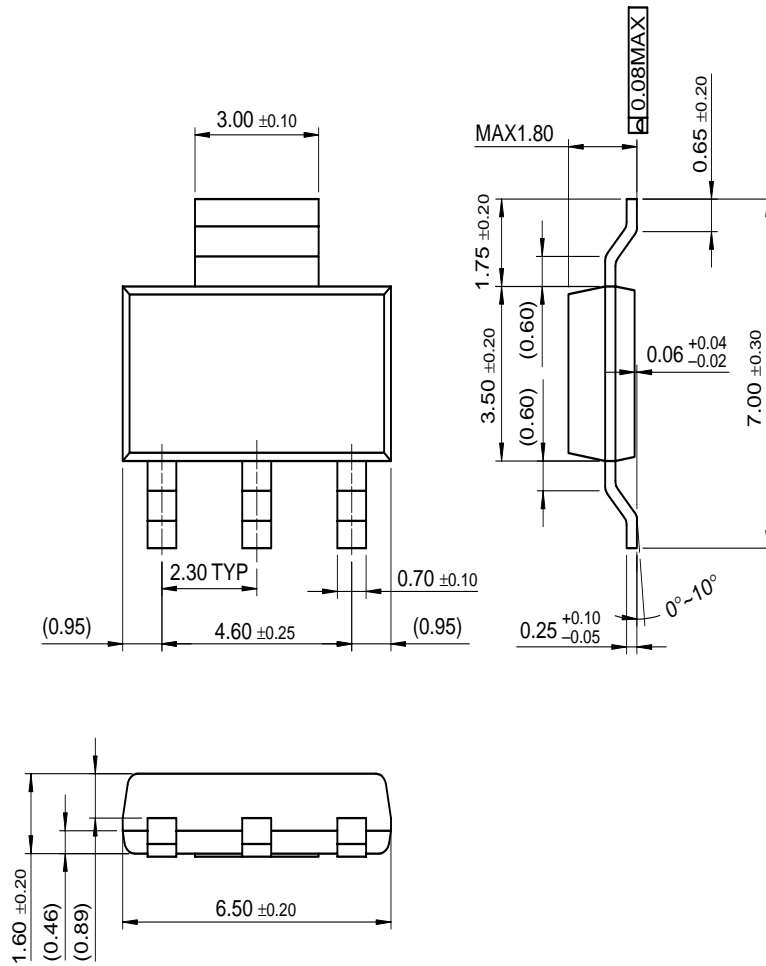
### Thermal Characteristics $T_A=25^\circ\text{C}$ unless otherwise noted

| Symbol          | Parameter   | Max.        | Units                      |
|-----------------|---|-------------|----------------------------|
| $P_D$           | Total Device Dissipation<br>Derate above $25^\circ\text{C}$ | 1000<br>8.0 | mW<br>mW/ $^\circ\text{C}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient                     | 125         | $^\circ\text{C}/\text{W}$  |

# Package Dimensions

BSP52

## SOT-223



Dimensions in Millimeters

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| Bottomless <sup>TM</sup>          | FRFET <sup>TM</sup>              | OPTOPLANAR <sup>TM</sup>         | SPM <sup>TM</sup>            |                   |
| CoolFET <sup>TM</sup>             | GlobalOptoisolator <sup>TM</sup> | PACMAN <sup>TM</sup>             | Stealth <sup>TM</sup>        |                   |
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